

N-channel TrenchMOS standard level FET 25 August 2014

Product data sheet

1. General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

2. Features and benefits

- AEC Q101 compliant
- Low conduction losses due to low on-state resistance
- Suitable for standard level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

3. Applications

- 12 V and 24 V loads
- Automotive and general purpose power switching
- Motors, lamps and solenoids

4. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	55	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u> ; <u>Fig. 3</u>	-	-	20.3	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>	-	-	62	W
Static chara	acteristics	·	1			
-0301	drain-source on-state resistance	V _{GS} = 10 V; I _D = 10 A; T _j = 175 °C; Fig. 11; Fig. 12	-	-	150	mΩ
		V _{GS} = 10 V; I _D = 10 A; T _j = 25 °C; Fig. 11; Fig. 12	-	64	75	mΩ
Avalanche	ruggedness		1			
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	$\begin{split} I_D &= 11 \text{ A}; \text{V}_{sup} \leq 55 \text{ V}; \text{R}_{GS} = 50 \Omega; \\ \text{V}_{GS} &= 10 \text{V}; \text{T}_{j(\text{init})} = 25 ^{\circ}\text{C}; \text{ unclamped} \end{split}$	-	-	30.3	mJ

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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D
2	D	drain		
3	S	source		G-UFA
mb	D	mounting base; connected to drain	D2PAK (SOT404)	mbb076 S

6. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
BUK7675-55A	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404			

7. Marking

Table 4. Marking codes	
Type number	Marking code
BUK7675-55A	BUK7675-55A

8. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$	-	55	V
V _{DGR}	drain-gate voltage	R _{GS} = 20 kΩ	-	55	V
V _{GS}	gate-source voltage		-20	20	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>	-	62	W
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; <u>Fig. 2</u> ; <u>Fig. 3</u>	-	20.3	А
		T _{mb} = 100 °C; V _{GS} = 10 V; <u>Fig. 2</u>	-	14.3	А
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \ \mu$ s; Fig. 3	-	81	А
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
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BUK7675-55A

03aa24

150 200 T_{mb} (°C)

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Symbol	Parameter	Conditions		Min	Мах	Unit
Source-drain diode						
I _S	source current	T _{mb} = 25 °C		-	20.3	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$		-	81	А
Avalanche ruggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 11 A; V_{sup} ≤ 55 V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped		-	30.3	mJ

120

80

40

0

0

l_{der} (%)

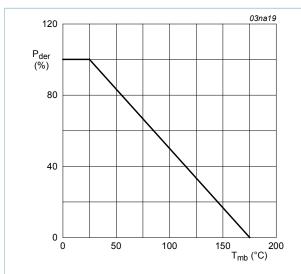
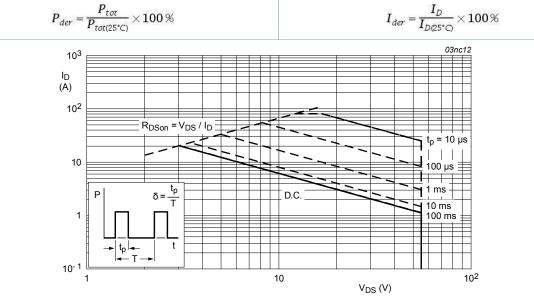


Fig. 1. Normalized total power dissipation as a function of mounting base temperature





 $T_{mb} = 25^{\circ}C; I_{DM}$ is single pulse

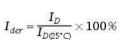
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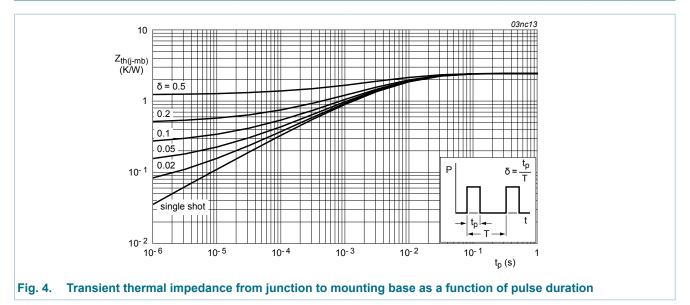
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9. Thermal characteristics

Table 6. 1	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. <u>4</u>	-	-	2.4	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	mounted on printed-circuit board; minimum footprint	-	50	-	K/W



10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	octeristics		I			-,,,,,,,,,,
V _{(BR)DSS}	drain-source	I_D = 0.25 mA; V_{GS} = 0 V; T_j = 25 °C	55	-	-	V
breakdown voltage		I_D = 0.25 mA; V_{GS} = 0 V; T_j = -55 °C	50	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 10	1	-	-	V
		I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 25 °C; Fig. 10	2	3	4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 10	-	-	4.4	V
I _{DSS}	drain leakage current	V _{DS} = 55 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μA
		V _{DS} = 55 V; V _{GS} = 0 V; T _i = 25 °C	-	0.05	10	μA

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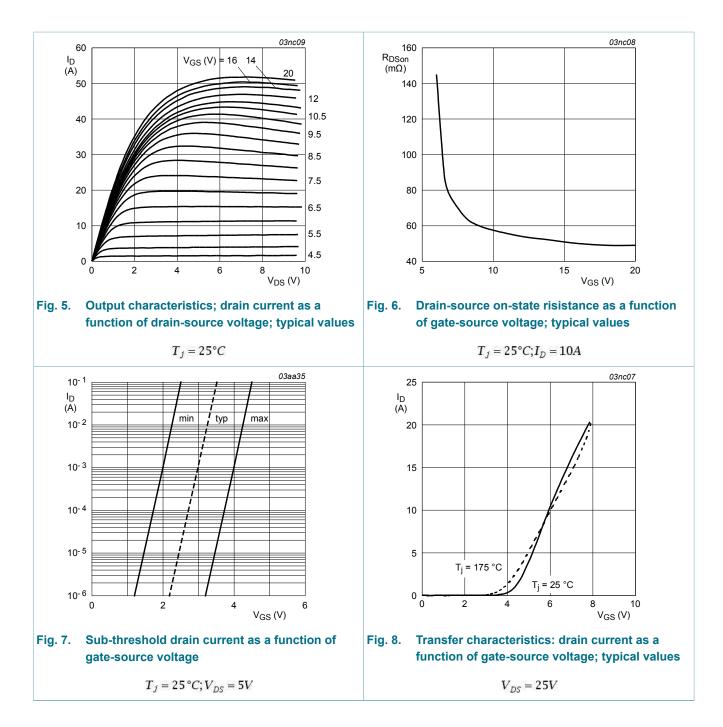
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N-channel TrenchMOS standard level FET

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{GSS}	gate leakage current	V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 10 A; T _j = 175 °C; Fig. 11; Fig. 12	-	-	150	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 10 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11; Fig. 12	-	64	75	mΩ
Dynamic cl	haracteristics					
C _{iss}	input capacitance	V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz;	-	320	483	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 13</u>	-	92	113	pF
C _{rss}	reverse transfer capacitance		-	64	90	pF
t _{d(on)}	turn-on delay time	V_{DS} = 30 V; R _L = 1.2 Ω; V _{GS} = 10 V; R _{G(ext)} = 10 Ω; T _j = 25 °C	-	10	-	ns
t _r	rise time		-	50	-	ns
t _{d(off)}	turn-off delay time		-	70	-	ns
t _f	fall time		-	40	-	ns
L _D	internal drain inductance	from upper edge of drain mounting base to centre of die; $T_j = 25 \text{ °C}$	-	2.5	-	nH
		from drain lead 6 mm from package to centre of die; $T_j = 25 \ ^{\circ}C$	-	4.5	-	nH
L _S	internal source inductance	from source lead to source bond pad; T _j = 25 °C	-	7.5	-	nH
Source-dra	in diode		I			
V _{SD}	source-drain voltage	I_{S} = 15 A; V_{GS} = 0 V; T_{j} = 25 °C; <u>Fig. 14</u>	-	0.85	1.2	V
t _{rr}	reverse recovery time	I_{S} = 20 A; dI _S /dt = -100 A/µs;	-	32	-	ns
Q _r	recovered charge	V_{GS} = -10 V; V_{DS} = 30 V; T_j = 25 °C	-	120	-	nC

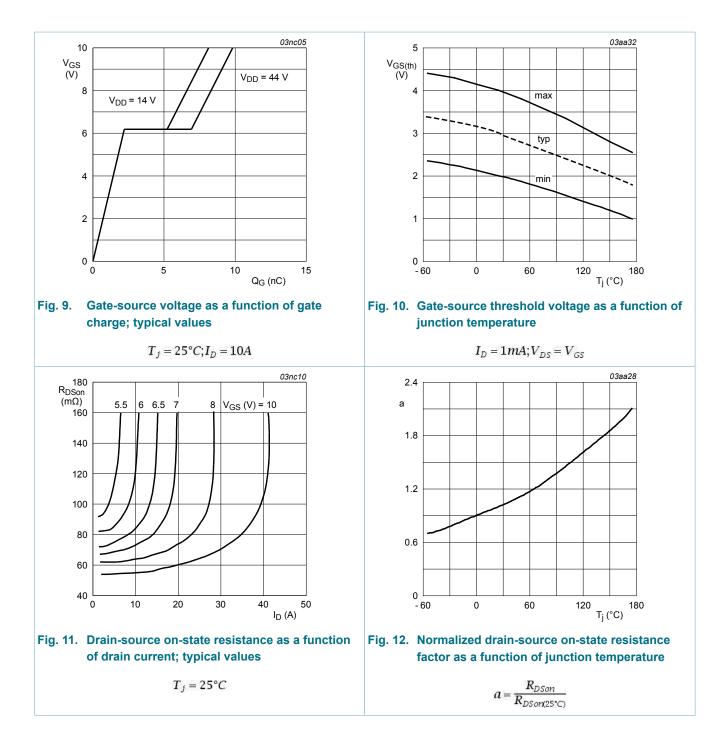
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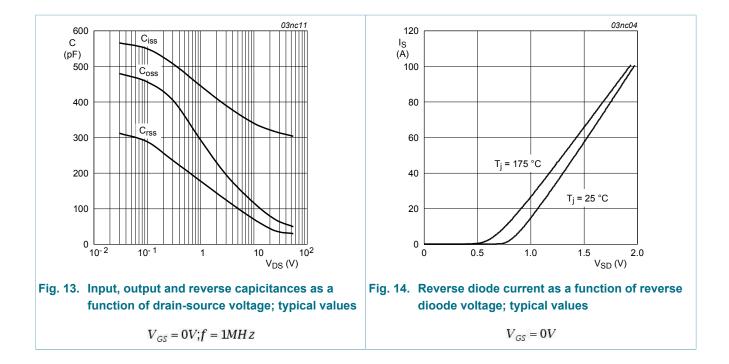
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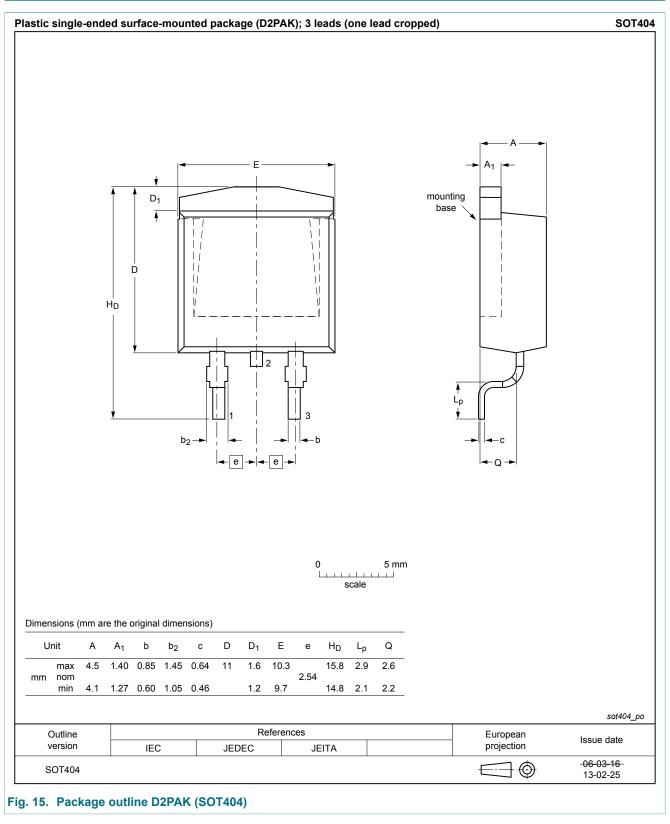
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11. Package outline



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12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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N-channel TrenchMOS standard level FET

13. Contents

General description	1
Features and benefits	1
Applications	1
Quick reference data	1
Pinning information	2
Ordering information	2
Marking	2
Limiting values	2
Thermal characteristics	4
Characteristics	4
Package outline	9
Legal information	10
Data sheet status	10
Definitions	10
Disclaimers	10
Trademarks	11
	Features and benefits

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